

ST2042

Enhanced power switch

Not recommended for new design

Features

- 80 mΩ high-side MOSFET switch
- 500 mA continuous current per channel
- Thermal and short-circuit protection with overcurrent logic output
- Operating range from 2.7 V to 5.5 V
- CMOS- and TTL-compatible enable inputs
- 10 ms OC_N fault-blanking
- 2.5 ms typical rise time
- Undervoltage lock out
- 10 μA maximum standby supply current
- Ambient temperature range, -40 °C to 85 °C
- Fault-blanking

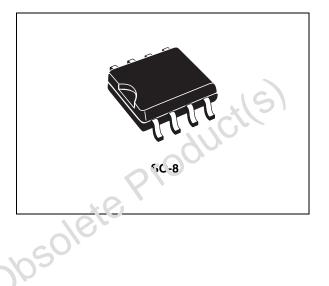
Table 1.Device summary

Order code	Package	Packaging
ST2042BD ⁽¹⁾	SO-8	Tube (50 parts per tube, 40 tube per box)
ST2042BP:9(1)	SO-8	Tape and reel (2500 parts per reel)

1. Not recommended for new design (refer to STMPS2242MTR). Contact ST sales office for availability.

November 2010

This is information on a product still in production but not recommended for new designs.



Contents

1	Description
2	Block diagram
3	Pin connections 5
4	Electrical ratings6
	4.1 Absolute maximum ratings
	4.2 Recommended operating conditions
5	Electrical characteristics
6	Package mechanical data 10
7	Revision history



1 Description

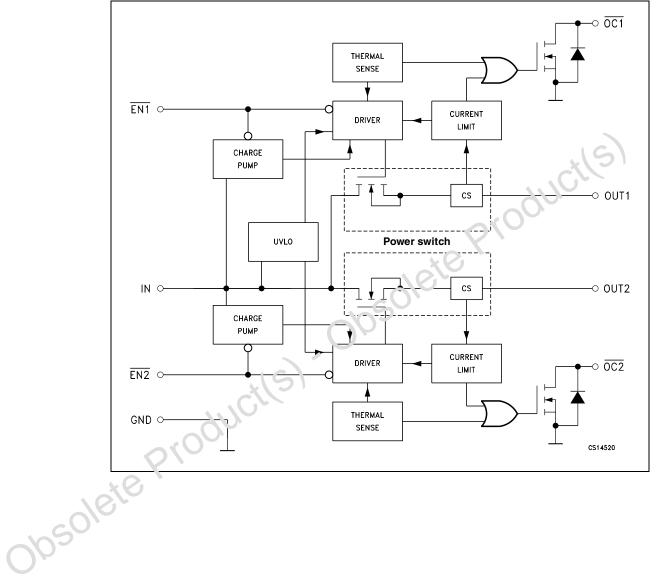
The ST2042 power distribution switches is intended for application where heavy capacitive loads and short-circuits are likely to be encountered. These devices incorporate 80 m Ω N-channel MOSFET high-side power switches for power-distribution systems that require multiple powers switches in a single package. Each switch is controlled by an independent logic enable input. Gate drive is provided by an internal charge pump designed to control the power-switch rise times and fall times to minimize current surges during switching. The charge pump requires no external components and allows operation from supplies as low as 2.7 V. When the output load exceeds the current-limit threshold or a short is present, these devices limit the output current to a safe level by switching into a constant-current mode, pulling the overcurrent (OCx) logic output low.

A 10 ms deglitching circuit provides fault-blanking feature, preventing the OC_N bits to be asserted during hot-insertion or short spikes of overcurrent conditions. When continuous heavy overloads and short circuits increase the power dissipation in the switch, causing the junction temperature to rise, a thermal protection circuit shuts off the switch or prevent damage. Recovery from a thermal shutdown is automatic once the derise has cooled sufficiently. Internal circuitry ensures the switch remains off until volic input voltage is present. These power-distribution switches are designed to current limit at 0.9 A.



2 Block diagram







3 Pin connections

Figure 2. Pin connections (top view)

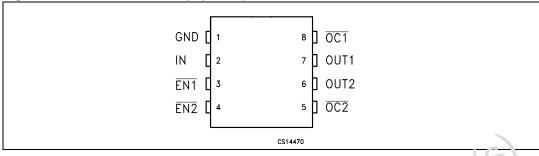


Table 2. Pin functions

	Pin	Symbol	Description
	1	GND	Ground
	2	IN	Input voltage
	3	EN1	Enable input. Log c ov turns on power switch IN-OUT1.
	4	EN2	Enable input. Logic low turns on power switch IN-OUT2.
	5	OC2	Overcurrent. Logic output active low IN-OUT2.
	6	OUT2	Pc war switch output
	7	OUT1	Power switch output
	8	021	Overcurrent. Logic output active low IN-OUT2
016	8 Bie Prodi	7000	



Electrical ratings 4

Absolute maximum ratings 4.1

Stressing the device above the rating listed in the "Absolute Maximum Ratings" table may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the Operating sections of this specification is not implied. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability. Refer also to the STMicroelectronics™ SURE program and other relevant quality documents.

Symbol	Parameter	Value	Unit
VI	Input voltage range ⁽¹⁾	-0.3 - 6	V
Vo	Output voltage range ⁽¹⁾	-0.3 - (V ₁ - 0.3)	V
V _{IENX}	EN Input voltage range	-0.3 to 6	V
۱ ₀	Continuous output current	Internally limited	
ESD	Electrostatic discharge	2	kV
Т _Ј	Junction operating temperature	-40 to 125	°C

Table 3. Absolute maximum ratings

1. All voltages are referred to GND.

Recommended operating conditions 4.2

Table 4. **Recommended operating conditions**

	Symbol	Parameter	Min.	Тур.	Max.	Unit
	V. (n.put voltage range ⁽¹⁾	2.7		5.5	V
Γ	Vo	Output voltage range ⁽¹⁾	0		5.5	V
10	l _o	Continuous output current (per switch)	0		500	mA
105014	. All voltage	s are referred to GND.				



Electrical characteristics 5

 V_I = 5.5 V, I_O = rated current, $V_{\overline{IEN}}$ = 0 V, T_J = 25 °C, unless otherwise specified (See *Note 1* on page 8).

Symbol	Parameter	Т	est conditions	Min.	Тур.	Max.	Unit
		V _I = 5 V	I _O = 0.5 A		80	100	
		V _I = 5 V	$I_{O} = 0.5 \text{ A}, \text{ T}_{J} = 85 ^{\circ}\text{C}$		90	120	
B	Static drain-source	V _I = 5 V	I _O = 0.5 A, T _J =125 °C		100	135	mΩ
R _{DS(on)}	^{DS(on)} ON-state resistance	V _I = 3.3 V	I _O = 0.5 A		90	25	11152
		V _I = 3.3 V	$I_{O} = 0.5 \text{ A}, \text{ T}_{J} = 85 ^{\circ}\text{C}$		110	:45	
		V _I = 3.3 V	$I_{O} = 0.5 \text{ A}, T_{J} = 125 ^{\circ}\text{C}$		120	160	
+	Output rise time	$V_{I} = 5.5 V$		530	2.5		ms
t _r		V _I = 2.7 V	$R_{\rm c} = 10 \ C_{\rm c} = 1 \ \mu E$		3		1115
t.	t _f Output fall time	$V_{I} = 5.5 V$	$R_{L} = 10, C_{L} = 1.0$		0.3		ms
t _f		$V_{ } = 2.7 V$			0.2		1115

Table 5. Power switch electrical characteristics

Enable Input ENx characteristics Table 6.

Symbo	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{IH}	High level input voltage	W₁ = 2.7 to 5.5 V	2			V
V.	Low level in _F ut	V _I = 4.5 to 5.5 V			0.8	v
V _{IL}	voltag ;	V _I = 2.7 to 4.5 V			0.4	v
Ц	Inoui current	V _{IENX} = 0 V or V _I	-0.5		0.5	μA
i v n	Turn-on time	R _L = 10 Ω, C _L = 100 μF			20	ms
t _{off}	Turn-off time	R _L = 10 Ω, C _L = 100 μF			40	ms
Table 7	Current limit ch	aracteristics				
Symbo	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{OS}	Short-circuit output current	$V_{I} = 5$ V, OUT connected to GND, device enabled into short circuit	0.7	1	1.3	А

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{OS}	Short-circuit output current	$V_I = 5 V$, OUT connected to GND, device enabled into short circuit	0.7	1	1.3	A



Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
	Current low level	$V_{IENX} = V_{I}$, no load,		0.025	1	μA
ISOL	output	$V_{IENX} = V_{I}$, no load, $T_{J} = -40$ to 125 °C			10	μΛ
	Current low high	V _{IENX} = 0, no load,		70	90	μA
I _{SOH} output		V_{IENX} = 0, no load, T_J = -40 to 125 °C			100	μΑ
١L	Output leakage current	$V_{IENX} = V_{I}$, output connected to GND, T _J = -40 to 125 °C			10	μA

 Table 8.
 Supply current characteristics

Table 9. Undervoltage characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Ма'л.	Unit
V _{IL}	Low level input voltage		2		2.5	V
V _{HYS}	Hysteresis			00.00		mV

Table 10. Overcurrent (OC) characteristics

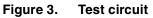
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{SINK}	Sink current	V _O = 5 V	10			mA
Vo	Output low voltage	I _O = 5 mA			0.5	V
I _{OFF}	OFF-state current	V _O = 5 V, V _O = 3.3 V			1	μA
T _{FB}	Fault-blanking period	V _I = 5.5 V, T _J = 25 °C (See <i>Note 2</i> and <i>Note 3</i>)	2	10		ms

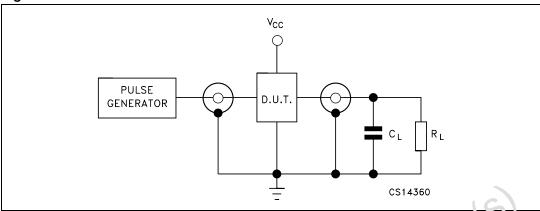
Note: 1 Pulse testing techniques maintain junction temperature close to ambient temperature: thermal offect must be takes into account separately.

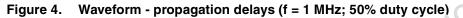
2 Specified by design, not production tested.

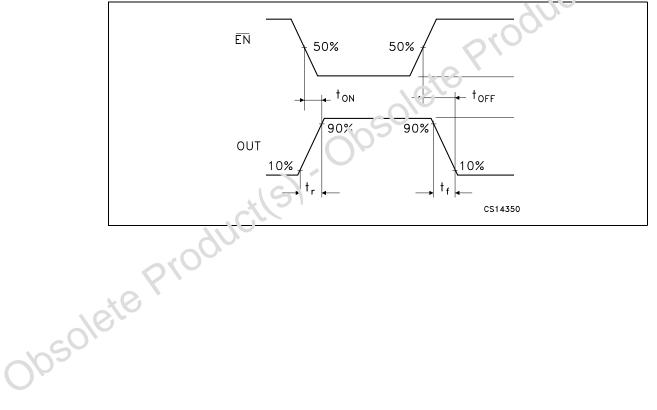
3 GLavanteed by design.













6 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

	Dim		mm.			inch	
	Dim.	Min.	Тур.	Max.	Min.	Тур.	Max.
	Α	1.35		1.75	0.053		5.06.7
	A1	0.10		0.25	0.004	Ċ	0.010
	A2	1.10		1.65	0.043	711	0.065
	В	0.33		0.51	0.013	0	0.020
	С	0.19		0.25	0.007		0.010
	D	4.80		5.00	0.189		0.197
	E	3.80		4.00	0.15		0.157
	е		1.27	SS SS		0.050	
	Н	5.80	(5.20	0.228		0.244
	h	0.25		0.50	0.010		0.020
	L	0.40	S	1.27	0.016		0.050
	k	C.		8° (n	nax.)		
	ddd	702		0.10			0.004
obsole	tepr	00					

Table 11. SO-8 mechanical data	Table 11.	SO-8 mechanical data
--	-----------	----------------------







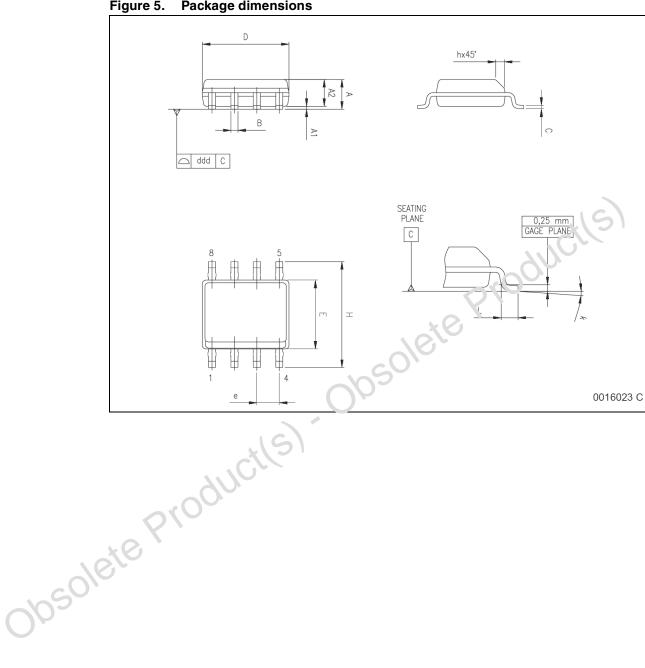


Figure 5. Package dimensions



7 Revision history

	Date	Revision	Changes		
	13-Jul-2005	4	Add bullet on pag. 1, add paragraph in the description on pag. 1 and add row $T_{\rm FB}$ on Table 10.		
	29-May-2007	5	Updated features in cover page, document reformatted.		
	24-Nov-2010	6	Document reformatted, added "Not Recommended for New Design" and <i>Note 1</i> below <i>Table 1</i> , corrected typo in <i>Features</i> , <i>Description</i> , <i>Figure 1</i> , <i>Table 2</i> to <i>Table 8</i> , <i>Table 10</i> , title cf <i>Figure 4</i> , updated <i>Table 1</i> , <i>Section 4.1</i> , <i>Section 5</i> and ECOPACK [®] text in <i>Section 6</i> .		
obsolete Product(s)					



Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries (SI") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services de_cribed herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property ignts is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warponcy covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein or considered as a warponcy covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein or considered the service of services or services or any intellectual property contained the service of the service of services or services or any intellectual property contained the service of services or services or any intellectual property contained the service of services or services or any intellectual property contained the service of services or services or any intellectual property contained the service of services or services or any intellectual property contained the service of services or services or any intellectual property contained the service of services or services or any intellectual property contained the service of service or services or services or service of service or service of service of service or service of service or service of service or service or service or service of service or service or

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS: FCm A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN VMMING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WANDANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTE OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROFENTIOR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE VISED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warran y granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2010 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan -Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com



Doc ID 9679 Rev 6